



# PBL6024D-Q

60 V, 1.5 A PNP loadswitch

20 October 2023

Product data sheet

## 1. General description

PNP low  $V_{CEsat}$  transistor and NPN Resistor- Equipped Transistor (RET) in a SOT457 (SC-74) small Surface-Mounted Device (SMD) plastic package.

## 2. Features and benefits

- Low  $V_{CEsat}$  and resistor-equipped transistor in one package
- Low threshold voltage ( $<1$  V) compared to MOSFET
- Space-saving solution
- Reduction of component count
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- Supply line switches
- Battery charger switches
- High-side switches for LEDs, drivers and backlights
- Portable equipment

## 4. Quick reference data

Table 1. Quick reference data

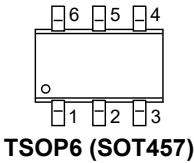
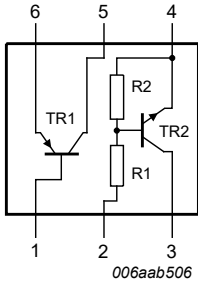
| Symbol  | Parameter                               | Conditions  | Min | Typ  | Max  | Unit    |
|---|---|---|-----|------|------|---------|
| <b>TR1; PNP low <math>V_{CEsat}</math> transistor</b> |   |   |     |      |      |         |
| $V_{CEO}$   | collector-emitter voltage               | open base   | -   | -    | -60  | V       |
| $I_C$   | collector current                       |   | -   | -    | -1.5 | A       |
| $I_{CM}$  | peak collector current                  | $t_p \leq 1$ ms; single pulse                           | -   | -    | -3   | A       |
| $R_{CEsat}$   | collector-emitter saturation resistance | $I_C = -1500$ mA; $I_B = -100$ mA;<br>$T_{amb} = 25$ °C | [1] | 110  | 175  | mΩ      |
| <b>TR2; NPN resistor-equipped transistor</b>          |   |   |     |      |      |         |
| $V_{CEO}$   | collector-emitter voltage               | open base   | -   | -    | 50   | V       |
| $I_O$   | output current                          |   | -   | -    | 100  | mA      |
| R1  | bias resistor 1 (input)                 |   | [2] | 15.4 | 22   | 28.6 kΩ |
| R2/R1   | bias resistor ratio                     |   | [2] | 0.8  | 1    | 1.2     |

[1] Pulse test:  $t_p \leq 300$  μs;  $\delta \leq 0.02$

[2] See "Section 11: Test information" for resistor calculation and test conditions.

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description            | Simplified outline  | Graphic symbol   |
|-----|--------|------------------------|---|--|
| 1   | B1     | base TR1               | <br>TSOP6 (SOT457) | <br>006aab506 |
| 2   | I2     | input (base) TR2       |   |  |
| 3   | O2     | output (collector) TR2 |   |  |
| 4   | GND    | GND (emitter) TR2      |   |  |
| 5   | C1     | collector TR1          |   |  |
| 6   | E1     | emitter TR1            |   |  |

6. Ordering information

Table 3. Ordering information

| Type number                 | Package |  |                        |
|-----------------------------|---------|--|------------------------|
|                             | Name    | Description  | Version                |
| <a href="#">PBLS6024D-Q</a> | TSOP6   | plastic, surface-mounted package (SC-74; TSOP6); 6 leads | <a href="#">SOT457</a> |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PBLS6024D-Q | KH           |

## 8. Limiting values

**Table 5. Limiting values**

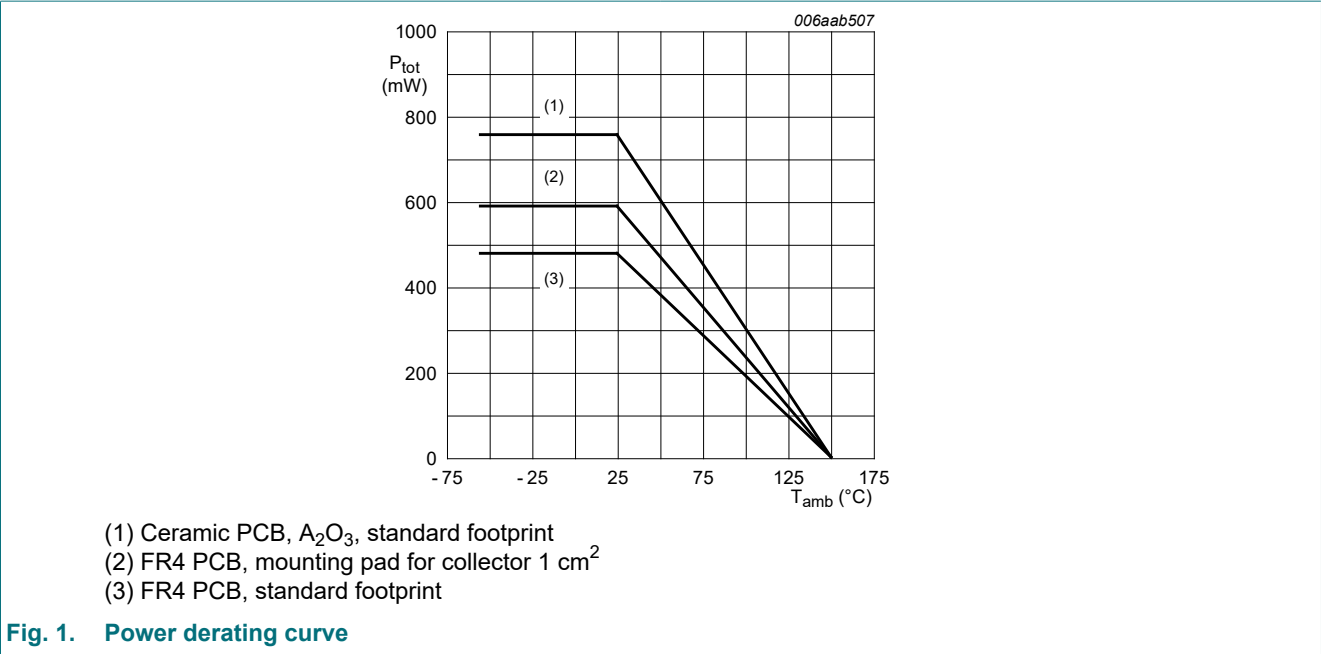
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                                     | Parameter                 | Conditions                          |                | Min | Max   | Unit |
|--|---------------------------|-------------------------------------|----------------|-----|-------|------|
| TR1; PNP low V <sub>CEsat</sub> transistor |                           |                                     |                |     |       |      |
| V <sub>CBO</sub>                           | collector-base voltage    | open emitter                        |                | -   | -60   | V    |
| V <sub>CEO</sub>                           | collector-emitter voltage | open base                           |                | -   | -60   | V    |
| V <sub>EBO</sub>                           | emitter-base voltage      | open collector                      |                | -   | -5    | V    |
| I <sub>C</sub>                             | collector current         |                                     |                | -   | -1.5  | A    |
| I <sub>CM</sub>                            | peak collector current    | t <sub>p</sub> ≤ 1 ms; single pulse |                | -   | -3    | A    |
| I <sub>B</sub>                             | base current              |                                     |                | -   | -300  | mA   |
| I <sub>BM</sub>                            | peak base current         | single pulse; t <sub>p</sub> ≤ 1 ms |                | -   | -1000 | mA   |
| P <sub>tot</sub>                           | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1]            | -   | 370   | mW   |
|  |                           |                                     | [2]            | -   | 480   | mW   |
|  |                           |                                     | [3]            | -   | 630   | mW   |
| TR2; NPN resistor-equipped transistor      |                           |                                     |                |     |       |      |
| V <sub>CBO</sub>                           | collector-base voltage    | open emitter                        |                | -   | 50    | V    |
| V <sub>CEO</sub>                           | collector-emitter voltage | open base                           |                | -   | 50    | V    |
| V <sub>EBO</sub>                           | emitter-base voltage      | open collector                      |                | -   | 10    | V    |
| V <sub>I</sub>                             | input voltage             | positive                            |                | -   | 40    | V    |
|  |                           | negative                            |                | -   | -10   | V    |
| I <sub>O</sub>                             | output current            |                                     |                | -   | 100   | mA   |
| I <sub>CM</sub>                            | peak collector current    | t <sub>p</sub> ≤ 1 ms; single pulse |                | -   | 100   | mA   |
| P <sub>tot</sub>                           | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] [2]<br>[3] | -   | 200   | mW   |
| Per device                                 |                           |                                     |                |     |       |      |
| P <sub>tot</sub>                           | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1]            | -   | 480   | mW   |
|  |                           |                                     | [2]            | -   | 590   | mW   |
|  |                           |                                     | [3]            | -   | 760   | mW   |
| T <sub>J</sub>                             | junction temperature      |                                     |                | -   | 150   | °C   |
| T <sub>amb</sub>                           | ambient temperature       |                                     |                | -55 | 150   | °C   |
| T <sub>stg</sub>                           | storage temperature       |                                     |                | -65 | 150   | °C   |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

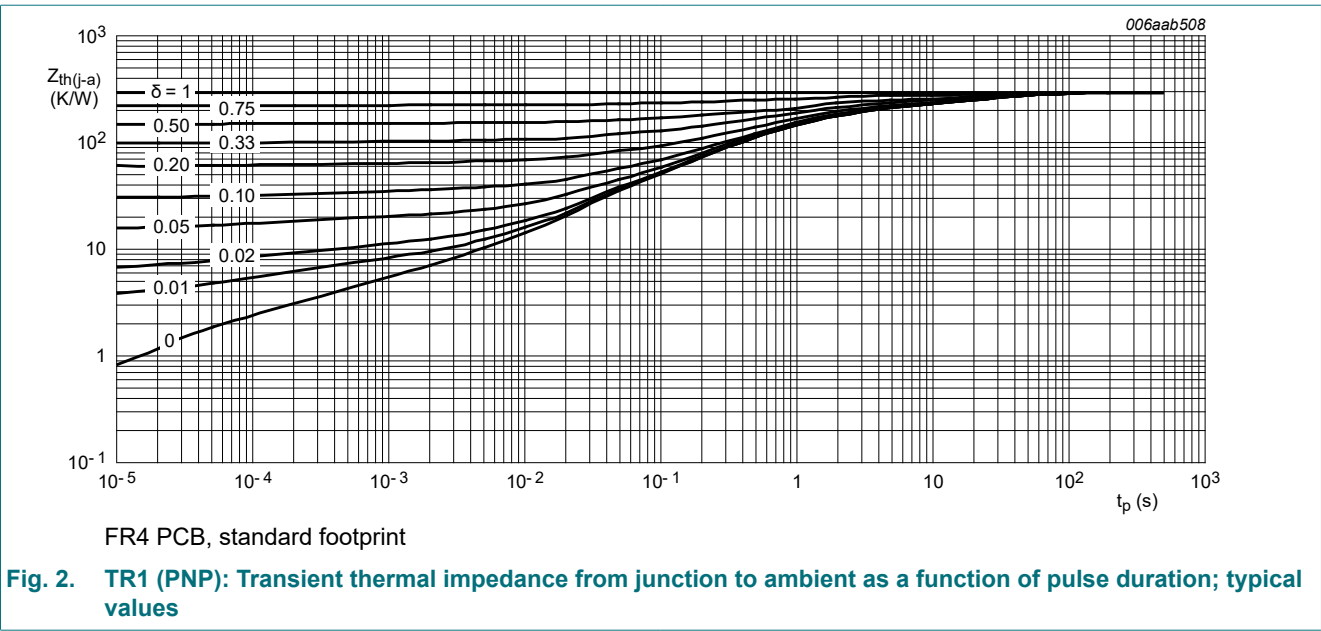


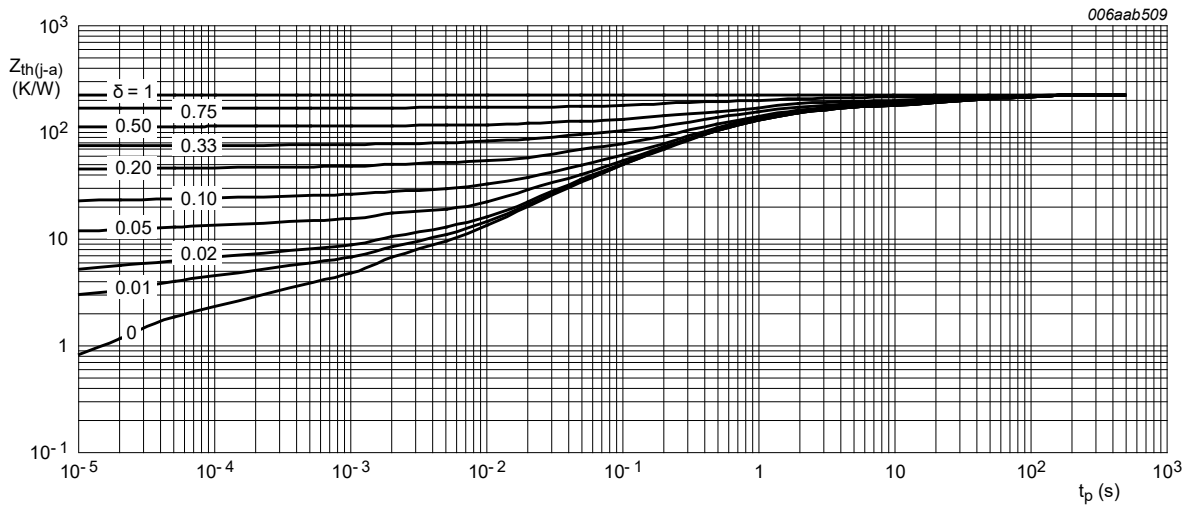
9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol                | Parameter  | Conditions  |     | Min | Typ | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| Per device            |  |             |     |     |     |     |      |
| R <sub>th(j-a)</sub>  | thermal resistance from junction to ambient      | in free air | [1] | -   | -   | 260 | K/W  |
|                       |  |             | [2] | -   | -   | 211 | K/W  |
|                       |  |             | [3] | -   | -   | 165 | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |             |     | -   | -   | 100 | K/W  |

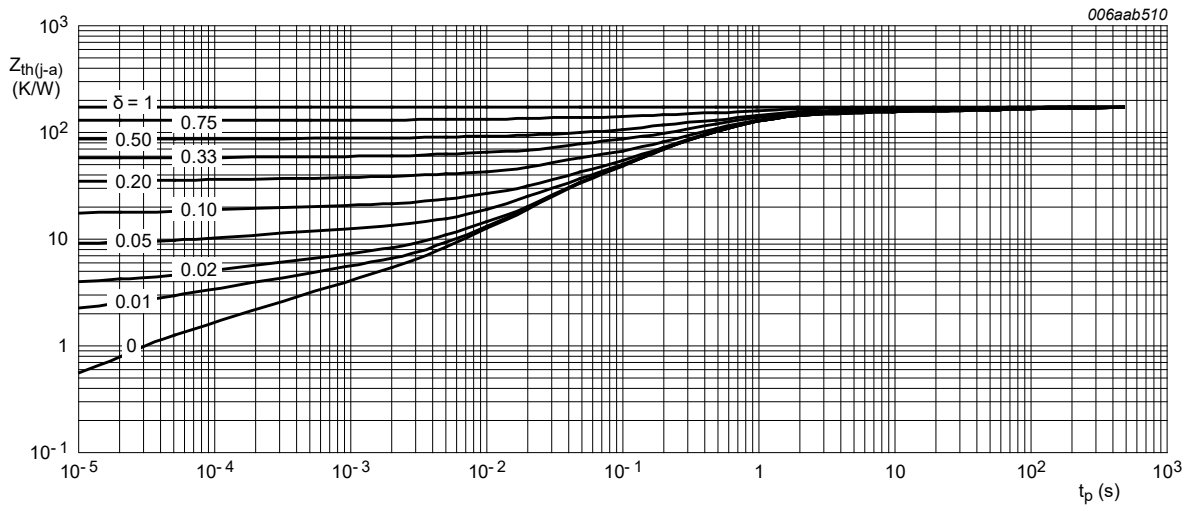
- [1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.  
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.  
[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.





FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>

Fig. 3. TR1 (PNP): Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

Fig. 4. TR1 (PNP): Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

Table 7. Characteristics

| Symbol  | Parameter                               | Conditions   |     | Min | Typ   | Max  | Unit |
|---|---|--|-----|-----|-------|------|------|
| <b>TR1; PNP low <math>V_{CEsat}</math> transistor</b> |   |  |     |     |       |      |      |
| $I_{CBO}$   | collector-base cut-off current          | $V_{CB} = -60\text{ V}; I_E = 0\text{ A}; T_{amb} = 25\text{ °C}$  |     | -   | -     | -100 | nA   |
|   |   | $V_{CB} = -60\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ °C}$   |     | -   | -     | -50  | μA   |
| $I_{CES}$   | collector-emitter cut-off current       | $V_{CE} = -48\text{ V}; T_{amb} = 25\text{ °C}; V_{BE} = 0\text{ A}$   |     | -   | -     | -100 | nA   |
| $I_{EBO}$   | emitter-base cut-off current            | $V_{EB} = -5\text{ V}; I_C = 0\text{ A}; T_{amb} = 25\text{ °C}$   |     | -   | -     | -100 | nA   |
| $h_{FE}$  | DC current gain                         | $V_{CE} = -2\text{ V}; I_C = -100\text{ mA}; T_{amb} = 25\text{ °C}$   |     | 180 | 285   | -    |      |
|   |   | $V_{CE} = -2\text{ V}; I_C = -500\text{ mA}; T_{amb} = 25\text{ °C}$   | [1] | 150 | 255   | -    |      |
|   |   | $V_{CE} = -2\text{ V}; I_C = -1\text{ A}; T_{amb} = 25\text{ °C}$  | [1] | 140 | 210   | -    |      |
|   |   | $V_{CE} = -2\text{ V}; I_C = -1.5\text{ A}; T_{amb} = 25\text{ °C}$  | [1] | 120 | 185   | -    |      |
| $V_{CEsat}$   | collector-emitter saturation voltage    | $I_B = -50\text{ mA}; T_{amb} = 25\text{ °C}; I_C = -0.5\text{ A}$   | [1] | -   | -65   | -100 | mV   |
|   |   | $I_B = -50\text{ mA}; T_{amb} = 25\text{ °C}; I_C = -1\text{ A}$   | [1] | -   | -130  | -200 | mV   |
|   |   | $I_B = -100\text{ mA}; T_{amb} = 25\text{ °C}; I_C = -1\text{ A}$  | [1] | -   | -110  | -170 | mV   |
|   |   | $I_B = -100\text{ mA}; T_{amb} = 25\text{ °C}; I_C = -1.5\text{ A}$  | [1] | -   | -165  | -260 | mV   |
| $R_{CEsat}$   | collector-emitter saturation resistance | $I_C = -1000\text{ mA}; I_B = -100\text{ mA}; T_{amb} = 25\text{ °C}$  | [1] | -   | 110   | 170  | mΩ   |
|   |   | $I_C = -1500\text{ mA}; I_B = -100\text{ mA}; T_{amb} = 25\text{ °C}$  | [1] | -   | 110   | 175  | mΩ   |
| $V_{BEsat}$   | base-emitter saturation voltage         | $I_C = -500\text{ mA}; I_B = -50\text{ mA}; T_{amb} = 25\text{ °C}$  | [1] | -   | -0.85 | -1   | V    |
|   |   | $I_C = -1500\text{ mA}; I_B = -100\text{ mA}; T_{amb} = 25\text{ °C}$  | [1] | -   | -0.93 | -1.1 | V    |
| $V_{BEon}$  | base-emitter turn-on voltage            | $V_{CE} = -10\text{ V}; I_C = -1000\text{ mA}; T_{amb} = 25\text{ °C}$   | [1] | -   | -0.75 | -1.1 | V    |
| $t_d$   | delay time                              | $V_{CC} = -10\text{ V}; I_C = -1\text{ A}; I_{Bon} = -50\text{ mA}; I_{Boff} = 50\text{ mA}; T_{amb} = 25\text{ °C}$ |     | -   | 17    | -    | ns   |
| $t_r$   | rise time                               |  |     | -   | 38    | -    | ns   |
| $t_{on}$  | turn-on time                            |  |     | -   | 55    | -    | ns   |
| $t_s$   | storage time                            |  |     | -   | 350   | -    | ns   |
| $t_f$   | fall time                               |  |     | -   | 65    | -    | ns   |
| $t_{off}$   | turn-off time                           |  |     | -   | 415   | -    | ns   |
| $C_c$   | collector capacitance                   | $V_{CB} = -10\text{ V}; I_E = 0\text{ A}; i_e = 0\text{ A}; f = 1\text{ MHz}; T_{amb} = 25\text{ °C}$                |     | -   | 30    | -    | pF   |
| $f_T$   | transition frequency                    | $V_{CE} = -10\text{ V}; I_C = -50\text{ mA}; f = 100\text{ MHz}; T_{amb} = 25\text{ °C}$                             |     | -   | 150   | -    | MHz  |
| <b>TR2; NPN resistor-equipped transistor</b>          |   |  |     |     |       |      |      |
| $I_{CBO}$   | collector-base cut-off current          | $V_{CB} = 50\text{ V}; I_E = 0\text{ A}; T_{amb} = 25\text{ °C}$   |     | -   | -     | 100  | nA   |
| $I_{CEO}$   | collector-emitter cut-off current       | $V_{CE} = 30\text{ V}; I_B = 0\text{ A}; T_{amb} = 25\text{ °C}$   |     | -   | -     | 1    | μA   |
|   |   | $V_{CE} = 30\text{ V}; I_B = 0\text{ A}; T_j = 150\text{ °C}$  |     | -   | -     | 50   | μA   |
| $I_{EBO}$   | emitter-base cut-off current            | $V_{EB} = 5\text{ V}; I_C = 0\text{ A}; T_{amb} = 25\text{ °C}$  |     | -   | -     | 180  | μA   |
| $h_{FE}$  | DC current gain                         | $V_{CE} = 5\text{ V}; I_C = 5\text{ mA}; T_{amb} = 25\text{ °C}$   |     | 60  | -     | -    |      |
| $V_{CEsat}$   | collector-emitter saturation voltage    | $I_C = 10\text{ mA}; I_B = 0.5\text{ mA}; T_{amb} = 25\text{ °C}$  |     | -   | -     | 150  | mV   |

| Symbol       | Parameter               | Conditions   | Min | Typ  | Max | Unit            |
|--------------|-------------------------|--|-----|------|-----|-----------------|
| $V_{I(off)}$ | off-state input voltage | $V_{CE} = 5\text{ V}$ ; $I_C = 100\text{ }\mu\text{A}$ ; $T_{amb} = 25\text{ }^\circ\text{C}$                                | -   | 1.1  | 0.8 | V               |
| $V_{I(on)}$  | on-state input voltage  | $V_{CE} = 0.3\text{ V}$ ; $I_C = 5\text{ mA}$ ; $T_{amb} = 25\text{ }^\circ\text{C}$   | 2.5 | 1.7  | -   | V               |
| R1           | bias resistor 1 (input) |  | [2] | 15.4 | 22  | 28.6 k $\Omega$ |
| R2/R1        | bias resistor ratio     |  | [2] | 0.8  | 1   | 1.2             |
| $C_c$        | collector capacitance   | $V_{CB} = 10\text{ V}$ ; $I_E = 0\text{ A}$ ; $i_e = 0\text{ A}$ ; $f = 1\text{ MHz}$ ; $T_{amb} = 25\text{ }^\circ\text{C}$ | -   | -    | 2.5 | pF              |

[1] Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$   
[2] See "Section 11: Test information" for resistor calculation and test conditions.

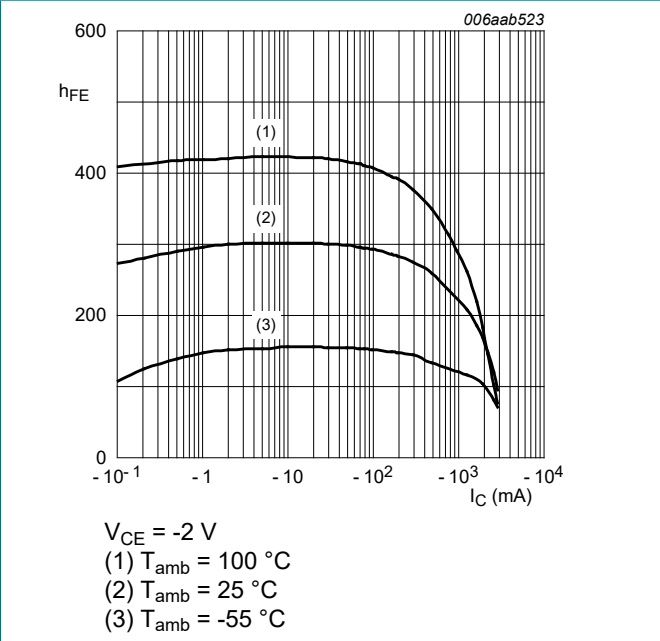


Fig. 5. TR1 (PNP): DC current gain as a function of collector current; typical values

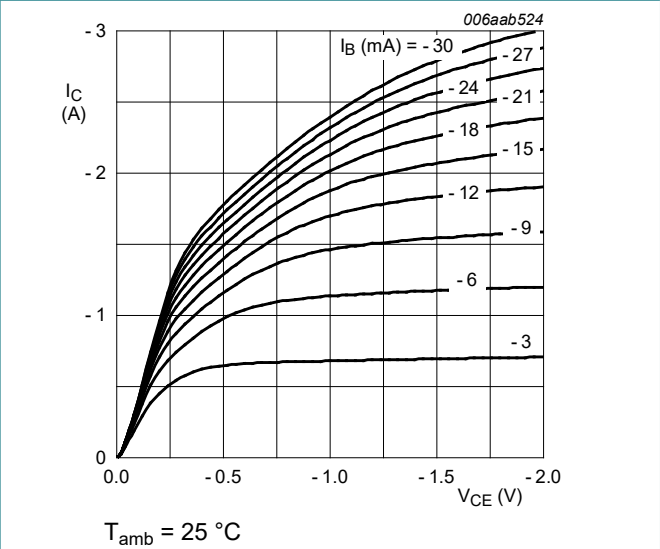


Fig. 6. TR1 (PNP): Collector current as a function of collector-emitter voltage; typical values

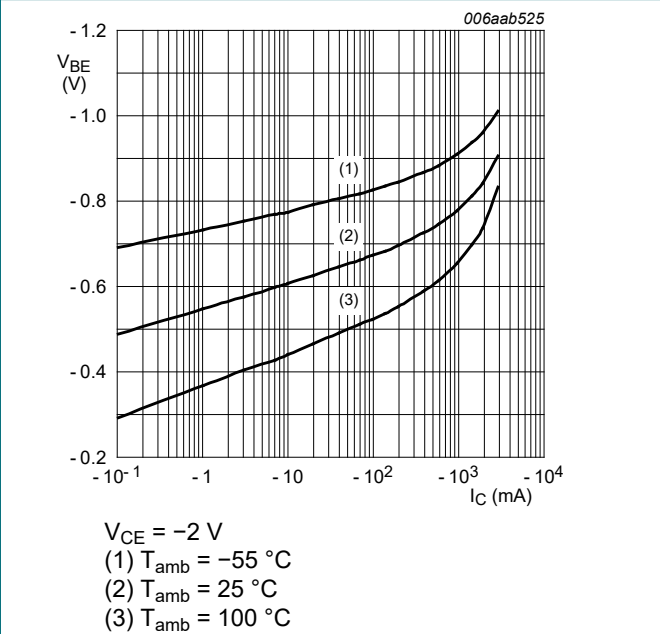


Fig. 7. TR1 (PNP): Base-emitter voltage as a function of collector current; typical values

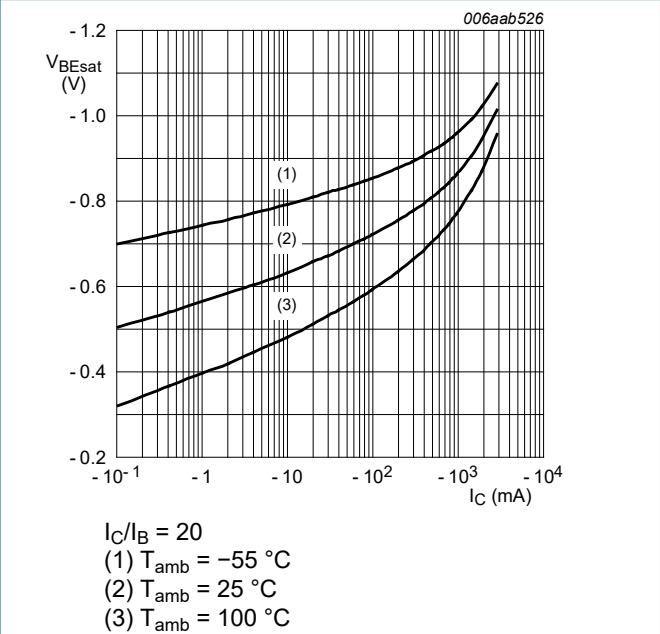


Fig. 8. TR1 (PNP): Base-emitter saturation voltage as a function of collector current; typical values

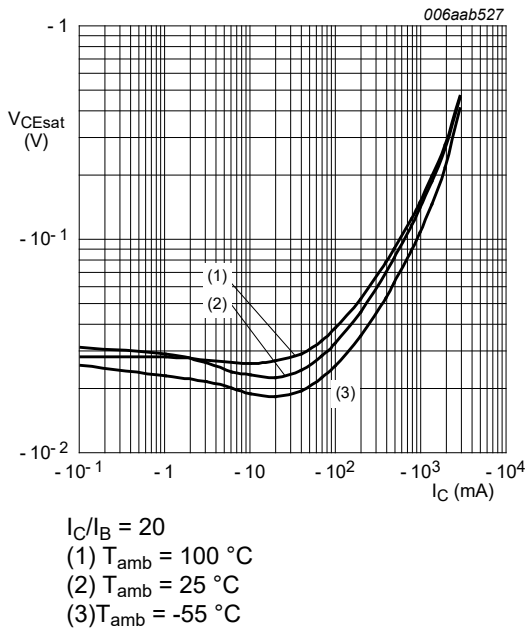


Fig. 9. TR1 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

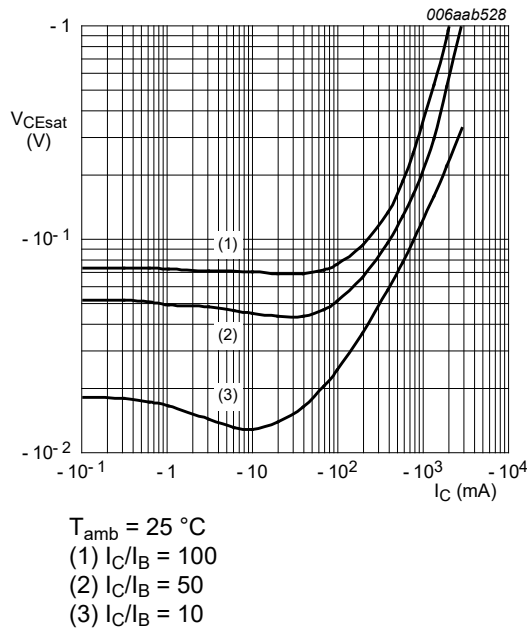


Fig. 10. TR1 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

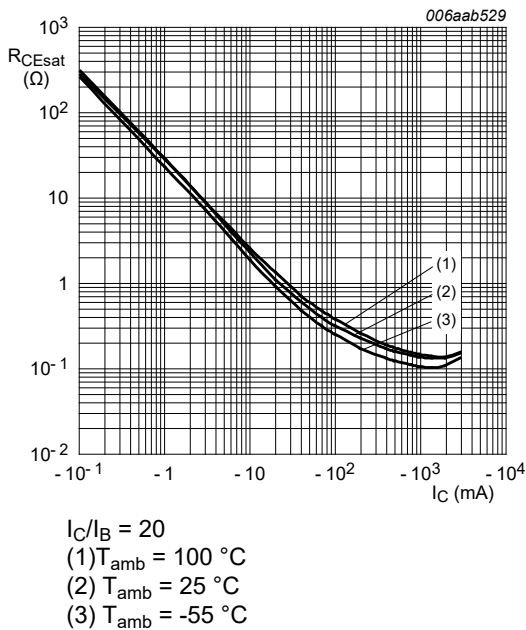


Fig. 11. TR1 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values

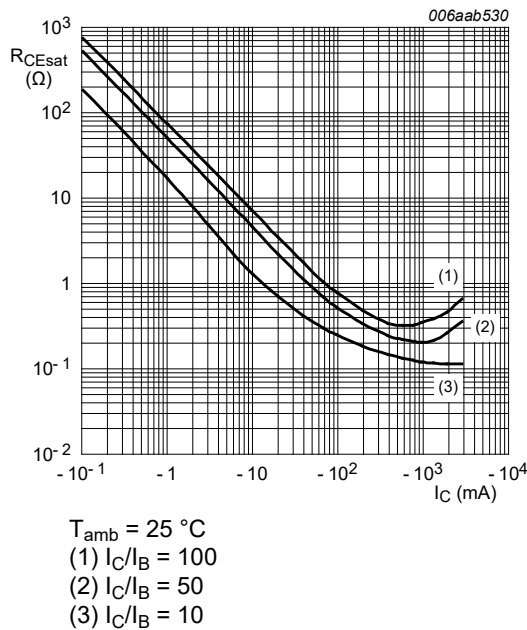


Fig. 12. TR1 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values



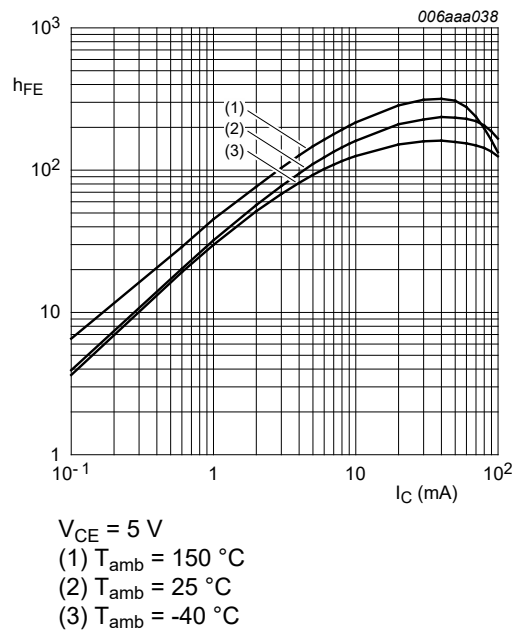


Fig. 13. TR2 (NPN): DC current gain as a function of collector current; typical values

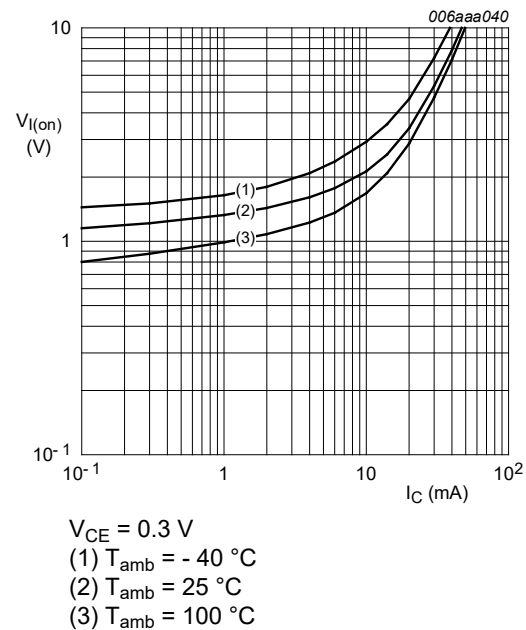


Fig. 14. TR2 (NPN): On-state input voltage as a function of collector current; typical values

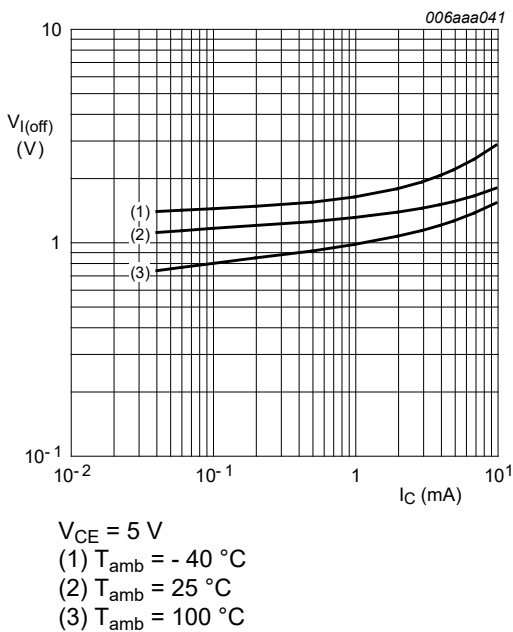


Fig. 15. TR2 (NPN): Off-state input voltage as a function of collector current; typical values

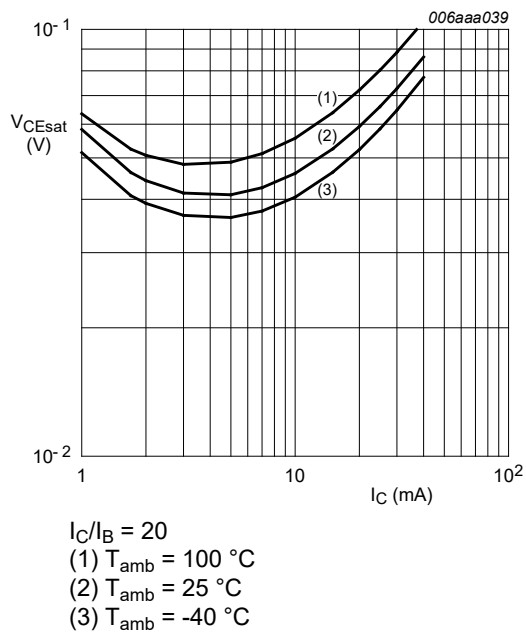
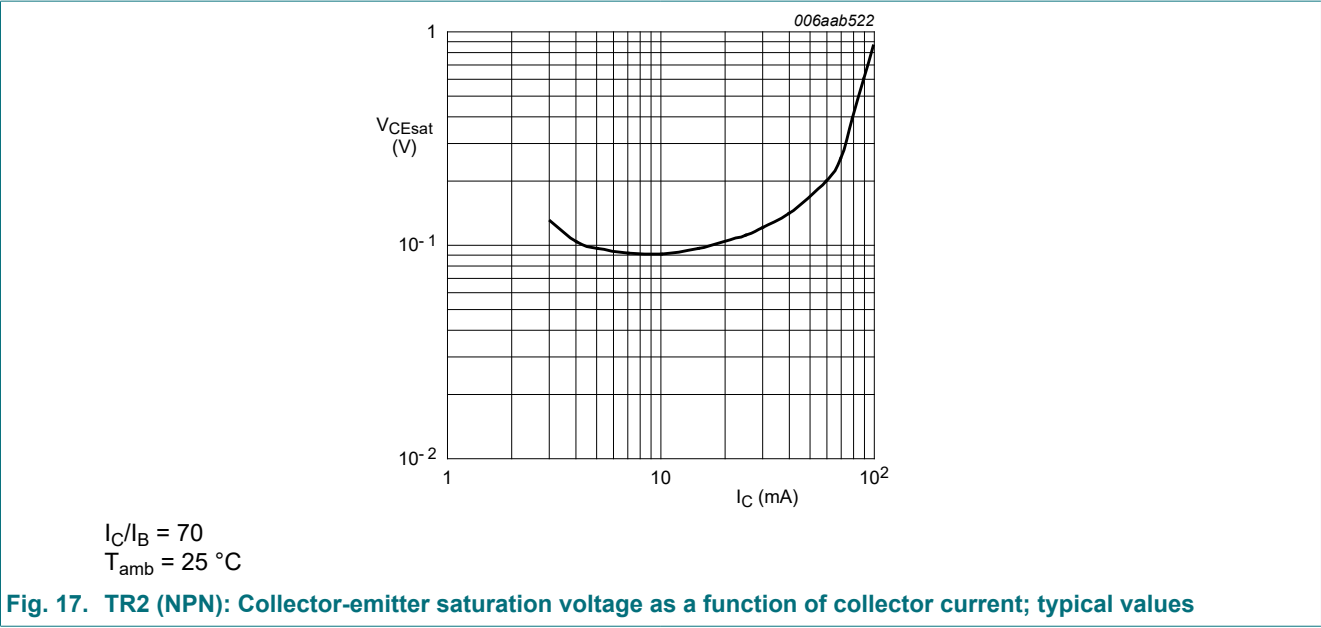


Fig. 16. TR2 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



11. Test information

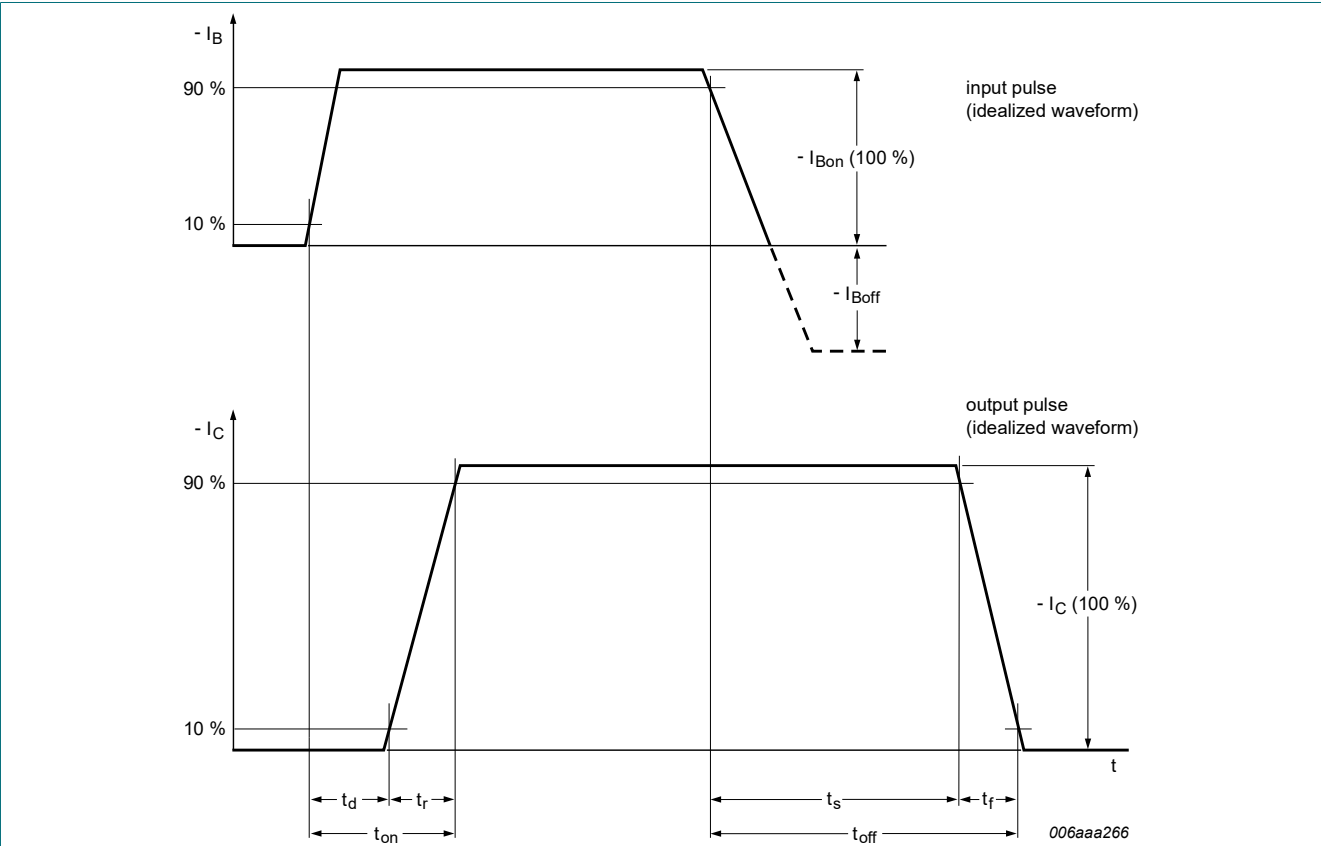


Fig. 18. TR1: Transistor switching time definition

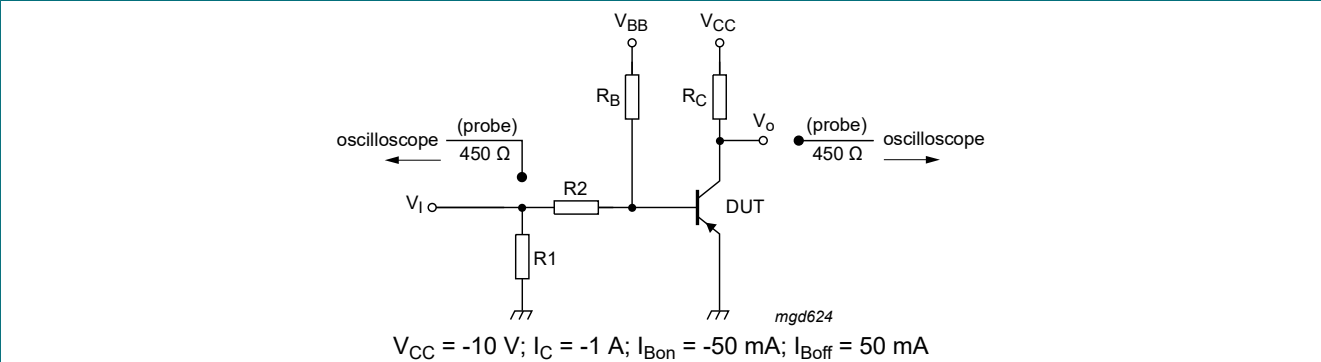
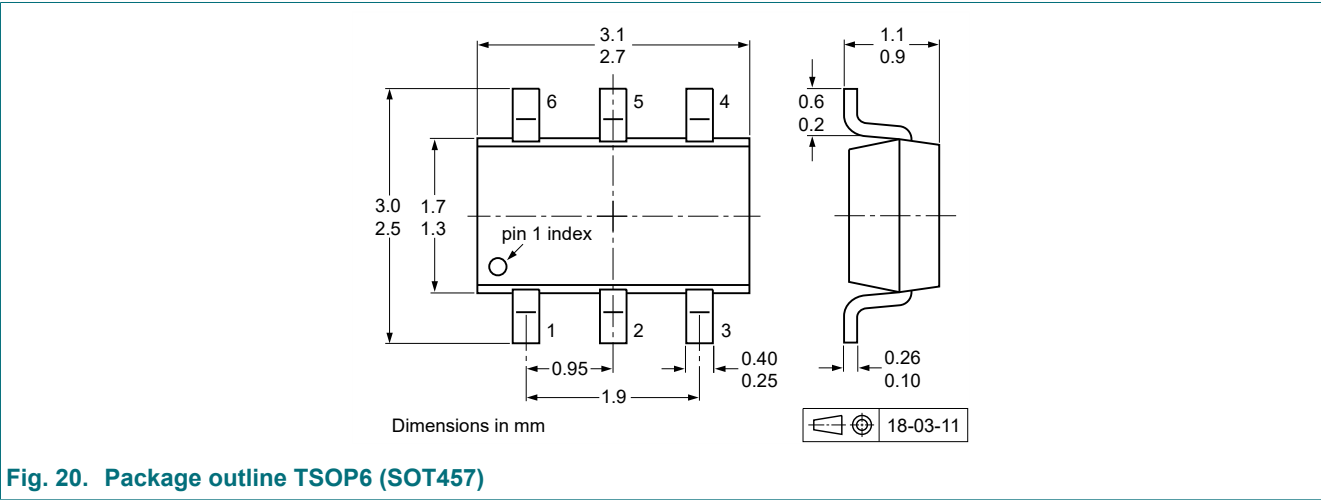


Fig. 19. TR1: Test circuit for switching times

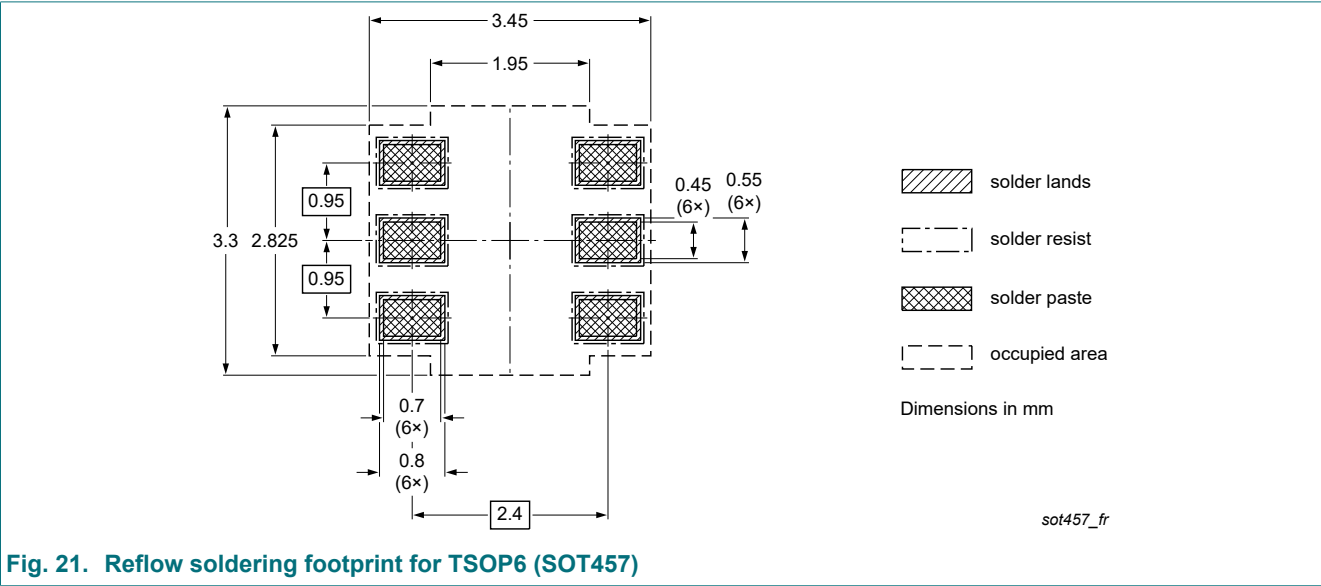
Quality information

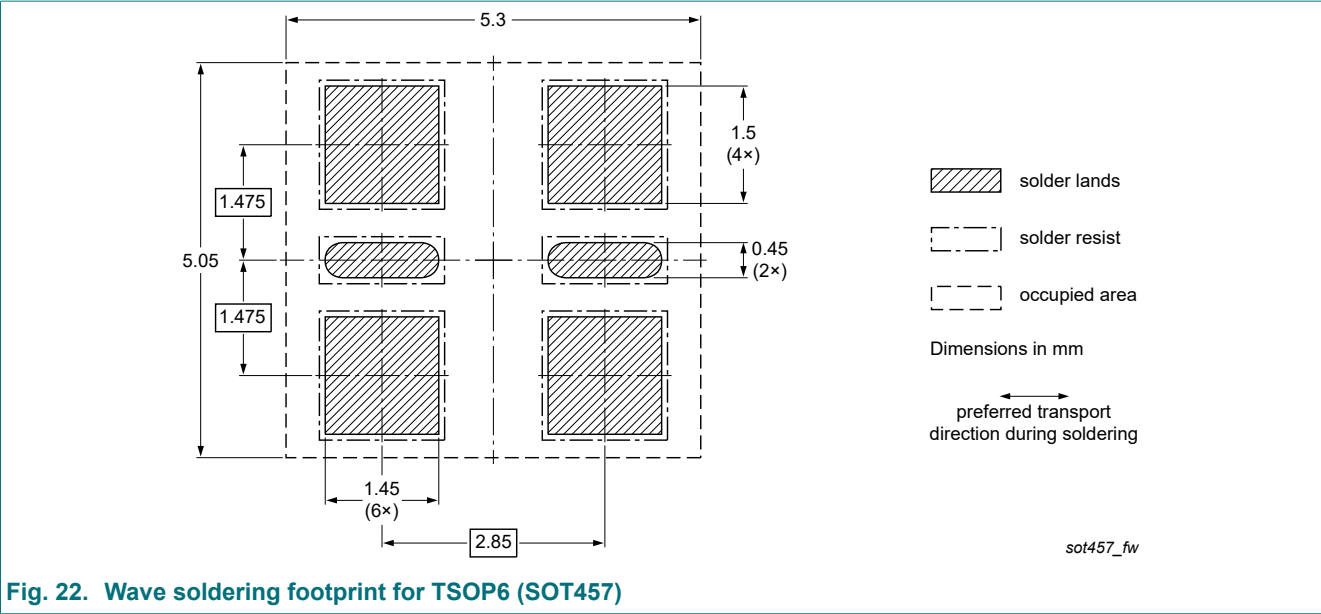
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



13. Soldering





14. Revision history

Table 8. Revision history

| Data sheet ID   | Release date | Data sheet status  | Change notice | Supersedes |
|-----------------|--------------|--------------------|---------------|------------|
| PBLS6024D-Q v.1 | 20231020     | Product data sheet | -             | -          |

## 15. Legal information

### Data sheet status

| Document status<br>[1][2]      | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <https://www.nexperia.com>.

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